DATA SHEET



NPN SILICON EPITAXIAL TRANSISTOR (DARLINGTON CONNECTION) FOR LOW-FREQUENCY POWER AMPLIFIERS AND LOW-SPEED HIGH-CURRENT SWITCHING

The 2SD2163 is a mold power transistor developed for lowspeed high-current switching. This transistor is ideal for direct driving from the IC output of devices such as pulse motor drivers and relay drivers of PC terminals.

FEATURES

NEC

- · Mold package that does not require an insulating board or insulation bushing
- · High DC current gain due to Darlington connection $h_{FE} = 1,000 \text{ MIN.} (@Ic = 10 \text{ A})$
- · Low collector saturation voltage: VCE(sat) = 1.5 V MAX. (@Ic = 10 A)

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	Vсво	150	V
Collector to emitter voltage	Vceo	100	V
Emitter to base voltage	Vebo	8.0	V
Collector current (DC)	IC(DC)	±10	А
Collector current (pulse)	C(pulse)*	±20	А
Base current (DC)	B(DC)	1.0	А
Total power dissipation	P⊤ (Tc = 25°C)	30	W
Total power dissipation	P⊤ (Ta = 25°C)	2.0	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

 $PW \le 10 \text{ ms}$, duty cycle $\le 50\%$

ELECTRICAL CHARACTERISTICS (Ta = 25° C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	$V_{CB} = 100 \text{ V}, \text{ I}_{E} = 0$			10	μA
DC current gain	hfe**	Vce = 2.0 V, Ic = 10 A	1,000	6,000	30,000	
Collector saturation voltage	V _{CE(sat)} **	Ic = 10 A, Iв = 25 mA		1.1	1.5	V
Base saturation voltage	VBE(sat)**	Ic = 10 A, Iв = 25 mA		1.8	2.0	V
Turn-on time	ton	$I_{C} = 10 \text{ A}, I_{B1} = -I_{B2} = 25 \text{ mA}$		1.0		μs
Storage time	t _{stg}	$R_L = 5.0 \Omega$, $V_{CC} \cong 50 V$		5.0		μs
Fall time	tr	Refer to the test circuit.		2.0		μs

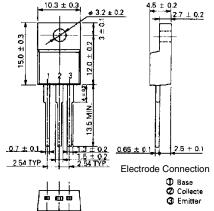
** Pulse test PW \leq 350 μ s, duty cycle \leq 2%

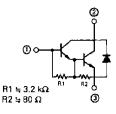
hfe CLASSIFICATION

Marking	М	L	К	J
hfe	1,000 to 3,000	2,000 to 5,000	4,000 to 10,000	8,000 to 30,000

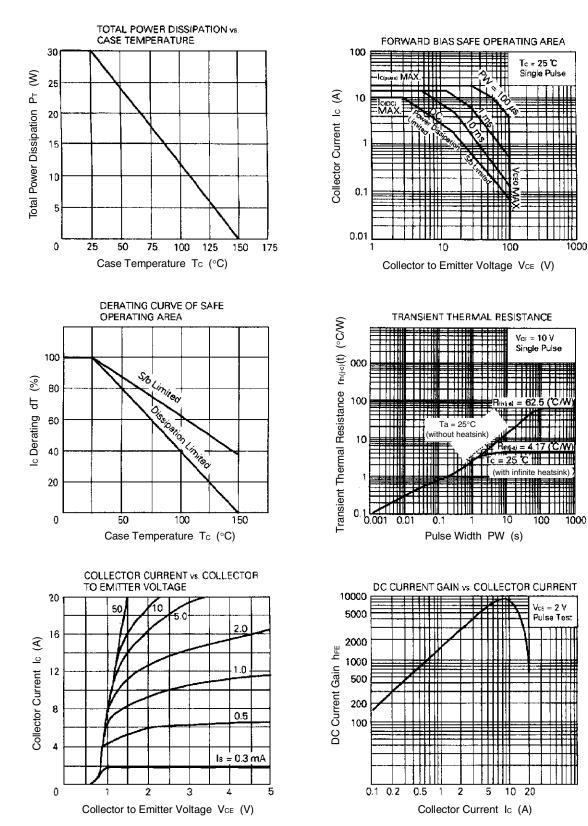
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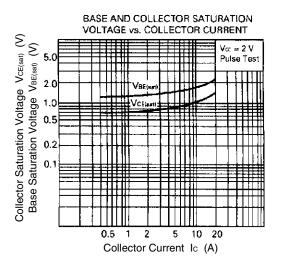
PACKAGE DRAWING (UNIT: mm)



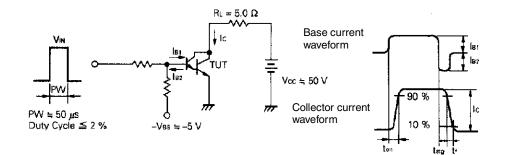


TYPICAL CHARACTERISTICS (Ta = 25°C)





SWITCHING TIME (ton, tstg, tf) TEST CIRCUIT



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